

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	920	eam	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 11:45	
2	BRS	L2	109	waveguide and 1	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 11:46	
3	BRS	L4	7	(optical near tap) and 3	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 11:48	
4	BRS	L3	91	semiconductor and 2	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:04	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	3429	(index near2 refraction) near4 different	USPAT; US-P GPUB ;EPO; JPO; DERW ENT; IBM_TDB	2004/07/06 12:21	
6	BRS	L6	5	3 and 5	USPAT; US-P GPUB ;EPO; JPO; DERW ENT; IBM_TDB	2004/07/06 12:05	
7	BRS	L7	20	(index near2 refraction) and 3	USPAT; US-P GPUB ;EPO; JPO; DERW ENT; IBM_TDB	2004/07/06 12:22	
8	BRS	L8	12965	((index near2 refraction) or (refractive near index)) near4 different)	USPAT; US-P GPUB ;EPO; JPO; DERW ENT; IBM_TDB	2004/07/06 12:23	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	9	3 and 8	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:49	
10	BRS	L10	50	eam and extinction near ratio	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:50	
11	BRS	L11	0	bias near voltsge and 10	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:50	
12	BRS	L12	0	bias near voltsge and 10	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:50	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	22	bias near voltage and 10	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:52	
14	BRS	L14	19	optical near signal and 13	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/07/0 6 12:52	